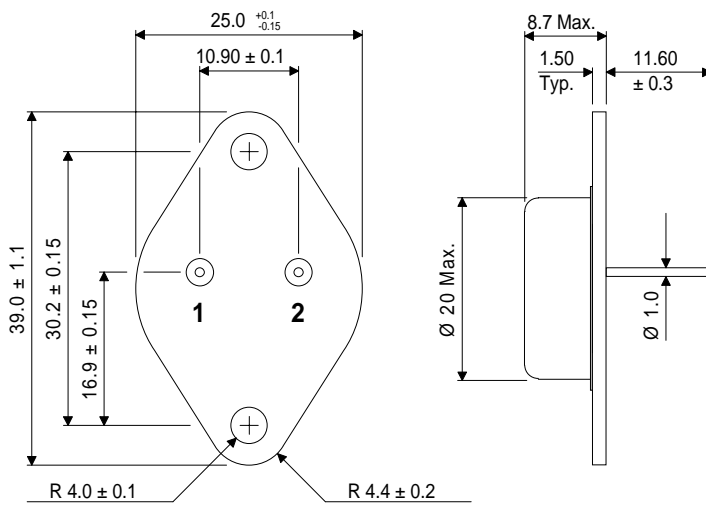


**MECHANICAL DATA**  
Dimensions in mm

**P-CHANNEL**  
**POWER MOSFET**



**POWER MOSFETS FOR**  
**AUDIO APPLICATIONS**

**FEATURES**

- HIGH SPEED SWITCHING
- P-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- N-CHANNEL ALSO AVAILABLE AS BUZ900D & BUZ901D
- DOUBLE DIE PACKAGE FOR MAXIMUM POWER AND HEATSINK SPACE

**TO-3**

Pin 1 – Gate

Pin 2 – Drain

Case – Source

**ABSOLUTE MAXIMUM RATINGS**

(T<sub>case</sub> = 25°C unless otherwise stated)

		<b>BUZ905D</b>	<b>BUZ906D</b>
V <sub>DSX</sub>	Drain – Source Voltage	-160V	-200V
V <sub>GSS</sub>	Gate – Source Voltage	±14V	
I <sub>D</sub>	Continuous Drain Current	-16A	
I <sub>D(PK)</sub>	Body Drain Diode	-16A	
P <sub>D</sub>	Total Power Dissipation @ T <sub>case</sub> = 25°C	250W	
T <sub>stg</sub>	Storage Temperature Range	-55 to 150°C	
T <sub>j</sub>	Maximum Operating Junction Temperature	150°C	
R <sub>θJC</sub>	Thermal Resistance Junction – Case	0.5°C/W	

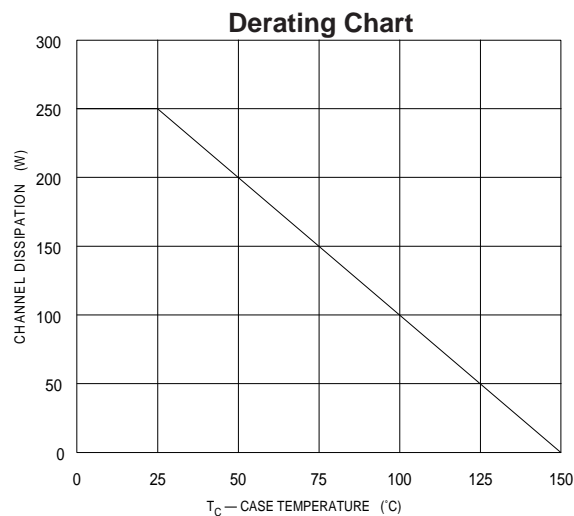
**STATIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV <sub>DSX</sub>	Drain – Source Breakdown Voltage	V <sub>GS</sub> = 10V	BUZ905D	-160			V
		I <sub>D</sub> = -10mA	BUZ906D	-200			
BV <sub>GSS</sub>	Gate – Source Breakdown Voltage	V <sub>DS</sub> = 0	I <sub>G</sub> = ±100µA	±14			V
V <sub>GS(OFF)</sub>	Gate – Source Cut-Off Voltage	V <sub>DS</sub> = -10V	I <sub>D</sub> = -100mA	-0.1		-1.5	V
V <sub>DS(SAT)*</sub>	Drain – Source Saturation Voltage	V <sub>GD</sub> = 0	I <sub>D</sub> = -16A			-12	V
I <sub>DSX</sub>	Drain – Source Cut-Off Current	V <sub>GS</sub> = 10V	V <sub>DS</sub> = -160V BUZ905D			-10	mA
			V <sub>DS</sub> = -200V BUZ906D			-10	
yfs*	Forward Transfer Admittance	V <sub>DS</sub> = -10V	I <sub>D</sub> = -3A	1.4		4	S

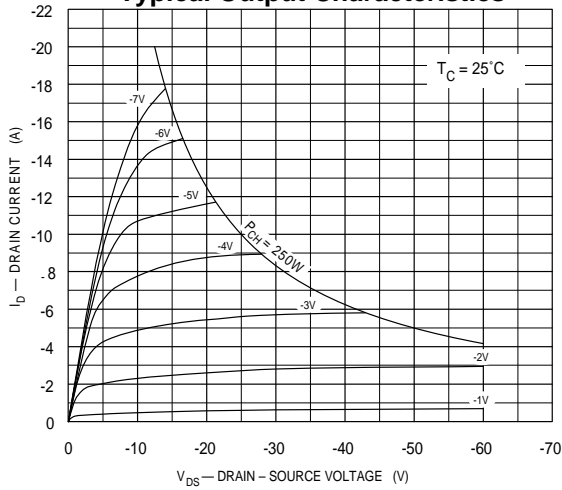
**DYNAMIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
C <sub>iSS</sub>	Input Capacitance	V <sub>DS</sub> = 10V f = 1MHz			1900		pF
C <sub>oss</sub>	Output Capacitance				900		
C <sub>rSS</sub>	Reverse Transfer Capacitance				60		
t <sub>on</sub>	Turn-on Time	V <sub>DS</sub> = 20V			150		ns
t <sub>off</sub>	Turn-off Time	I <sub>D</sub> = 7A			110		

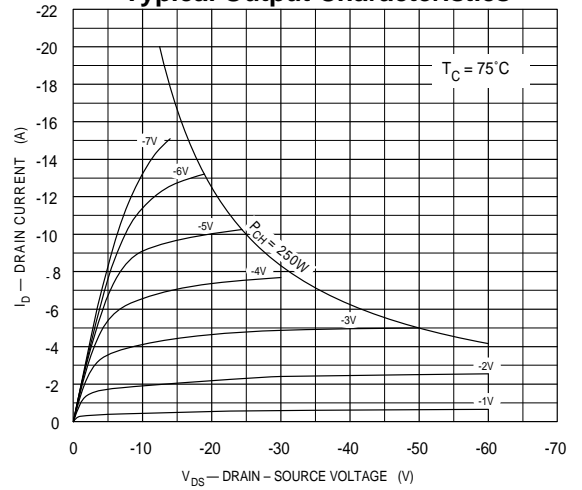
\* Pulse Test: Pulse Width = 300µs , Duty Cycle ≤ 2%.



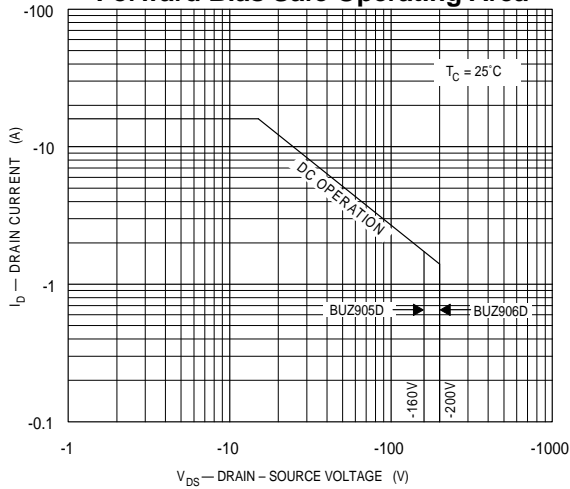
**Typical Output Characteristics**



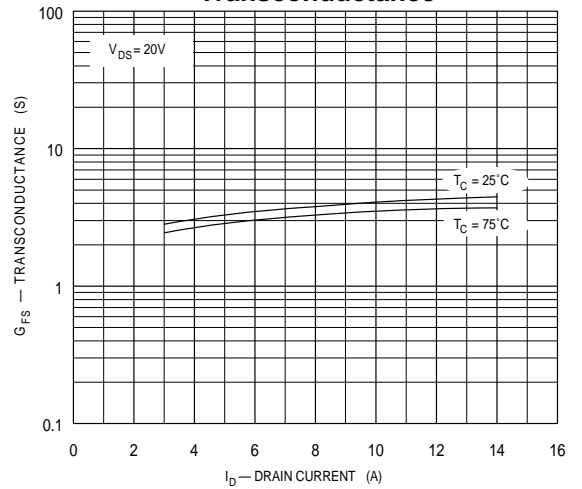
**Typical Output Characteristics**



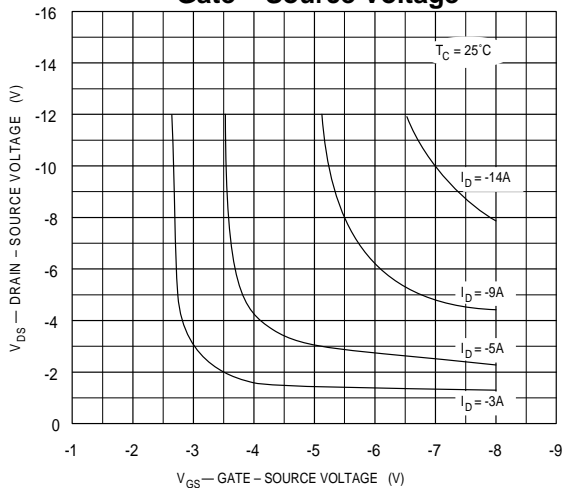
**Forward Bias Safe Operating Area**



**Transconductance**



**Drain - Source Voltage vs Gate - Source Voltage**



**Typical Transfer Characteristics**

